Steering the current flow in twisted bilayer graphene

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A nanoelectronic device made of twisted bilayer graphene (TBLG) is proposed to steer the direction of the current flow, see Figure 1. The ballistic electron current, injected at one edge of the bottom layer, can be guided predominantly to one of the lateral edges of the top layer. The current is steered to the opposite lateral edge, if either the twist angle is reversed or the electrons are injected in the valence band instead of the conduction band, making it possible to control the current flow by electric gates. When both graphene layers are aligned, the current passes straight through the system without changing its initial direction. The observed steering angle exceeds well the twist angle and emerges for a broad range of experimentally accessible parameters leading to a non-local resistance, see Figure 2. It is explained by the trigonal shape of the energy bands beyond the van Hove singularity due to the Moiré interference pattern. As the shape of the energy bands depends on the valley degree of freedom, the steered current is valley polarized. Our findings show how to control and manipulate the current flow in TBLG. Technologically, they are of relevance for applications in twistronics and valleytronics.

REFERENCES

[1] J. A. Sánchez-Sánchez, M. Navarro-Espino, Y. Betancur-Ocampo, J.E. Barrios-Vargas, T. Stegmann: Steering the current flow in twisted bilayer graphene, arXiv:2106.06514

FIGURES



Figure 1: Schematic representation of the studied TBLG device. Electrons are injected through contact *S* at the bottom layer and detected by three drain contacts $D_{1/1/2}$ at the top layer.



Figure 2: Longitudinal resistance R_{xx} and Hall Resistance R_{xy} as a function of energy for the TBLG device at a twist angle of θ =2.9°. The steering of the current flow to one of the lateral edges generates a non-local Hall resistance.